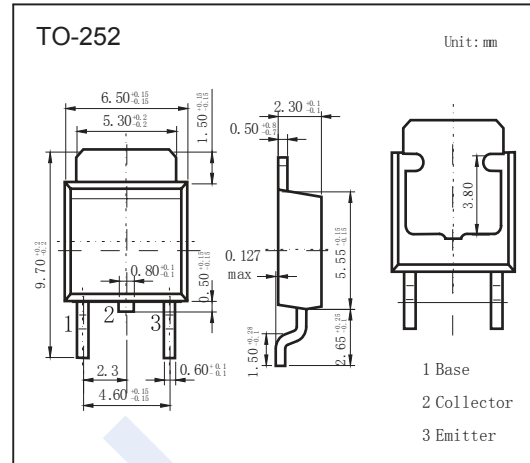


NPN Transistors

2SD2121

■ Features

- Low frequency power amplifier
- Complementary to 2SB1407

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	35	V
Collector - Emitter Voltage	V_{CE0}	35	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	2.5	A
Collector Current - Pulse	I_{CP}	3	
Collector Power Dissipation	P_C	18	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 1 \text{ mA}, I_E = 0$	35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 10 \text{ mA}, R_{BE} = \infty$	35			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 1 \text{ mA}, I_C = 0$	5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 35 \text{ V}, I_E = 0$			20	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5 \text{ V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 2 \text{ A}, I_B = 200 \text{ mA}$			1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A}$			1.5	
DC current gain	h_{FE}	$V_{CE} = 2 \text{ V}, I_C = 500 \text{ mA}$	60		320	
		$V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A}$	20			

■ Classification of $h_{FE(1)}$

Type	2SD2121-B	2SD2121-C	2SD2121-D
Range	60-120	100-200	160-320

NPN Transistors

2SD2121

■ Typical Characteristics

